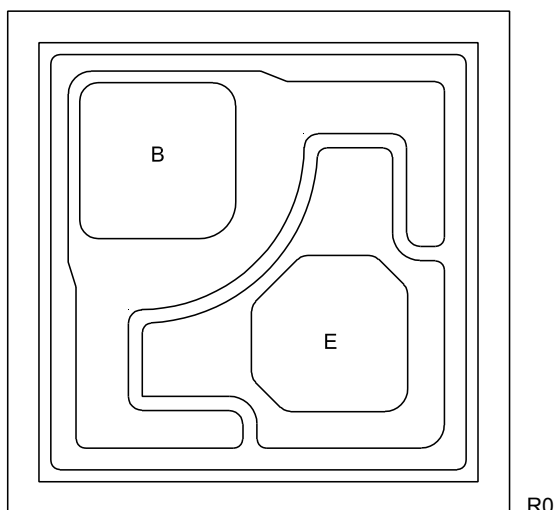


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.0 MILS
Base Bonding Pad Area	3.7 x 3.7 MILS
Emitter Bonding Pad Area	3.7 x 3.7 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

**GEOMETRY**



BACKSIDE COLLECTOR

**GROSS DIE PER 4 INCH WAFER**

93,826

**PRINCIPAL DEVICE TYPES**

2N3904  
CMKT3904  
CMLT3904E  
CMPT3904  
CMPT3904E  
CMST3904  
CXT3904  
CZT3904

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